Silicon NPN Power Transistors BU326 BU326A

DESCRIPTION

·With TO-3 package
·High voltage;high speed
·Low collector saturation voltage.

APPLICATIONS

·Intended for operating in CTV receiver's chopper supplies.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings (Tc=25□)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	BU326	Open emitter	800	V
		BU326A		900	
V_{CEO}	Collector-emitter voltage	BU326	Open base	375	V
		BU326A		400	
V_{EBO}	Emitter-base voltage		Open collector	10	V
I_C	Collector current			6	A
I_{CM}	Collector current-peak			8	A
I_B	Base current			3	A
P_T	Total power dissipation		T_C=25□	75	W
T_j	Junction temperature			-65~200	□
T_{stg}	Storage temperature			-65~200	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	2.33	□/W

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	BU326	I_C=0.1A; I_B=0	375			V
		BU326A		400			
$V_{CEsat-1}$	Collector-emitter saturation voltage		I_C=2.5 A;I_B=0.5A			1.5	V
$V_{CEsat-2}$	Collector-emitter saturation voltage		I_C=4A;I_B=1.25 A			3.0	V
$V_{BEsat-1}$	Base-emitter saturation voltage		I_C=2.5 A;I_B=0.5A			1.4	V
$V_{BEsat-2}$	Base-emitter saturation voltage		I_C=4A;I_B=1.25 A			1.6	V
I_{CES}	Collector cut-off current	BU326	V_{CE}=800V;V_{BE}=0			1	mA
		BU326A	V_{CE}=900V;V_{BE}=0				
I_{EBO}	Emitter cut-off current		V_{EB}=10V; I_C=0			10	mA
h_{FE}	DC current gain		I_C=1A ; V_{CE}=5V		25		
f_T	Transition frequency		I_C=0.2A ; V_{CE}=10V; f=1MHz	4.0			MHz

Switching times

t_{on}	Turn-on time	I_C=2.5A ; I_{B1}=0.5A;I_{B2}=-1A V_{CC}=250V ;			0.5	μs
t_s	Storage time				3.5	μs
t_f	Fall time				0.5	μs

PACKAGE OUTLINE

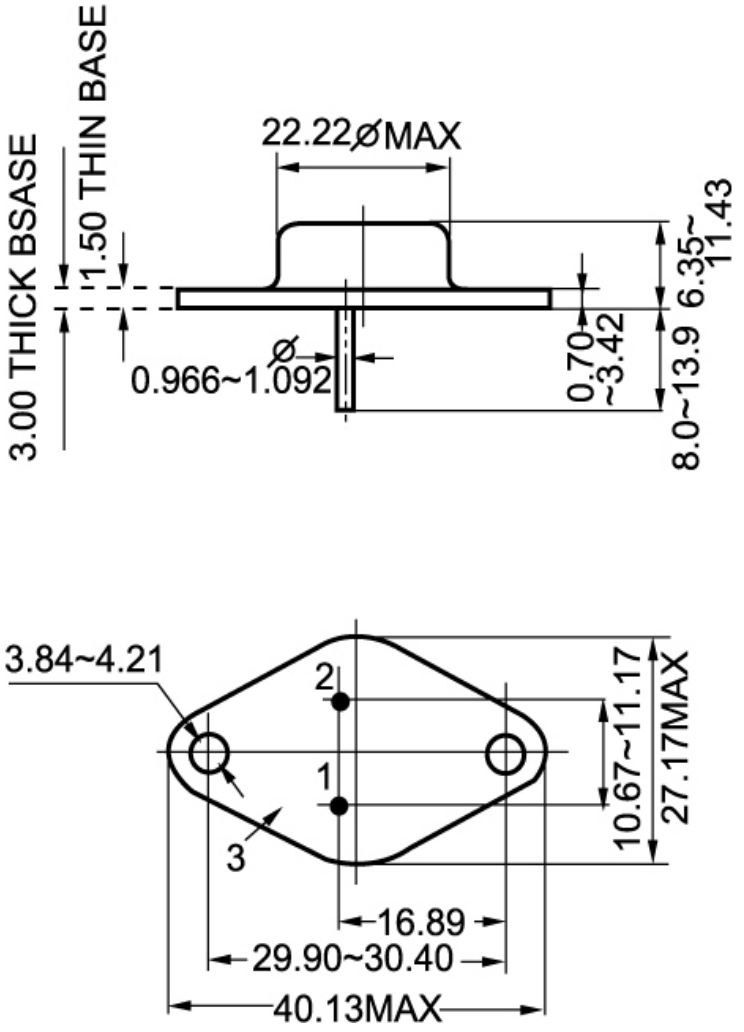

Fig.2 Outline dimensions